Exam. Code: 0929 Sub. Code: 6909

Max. Marks: 50

## 1128

## B.E. (Electronics and Communication Engineering) Fifth Semester EC-501: VLSI Design

Time allowed: 3 Hours NOTE: Attempt five questions in all, including Question No. I which is compulsory and selecting

two questions from each Part.

Q1)	<ul><li>a) What are the sources of leakage power dissipation in MOSFET?</li><li>b) What are the factors that make Si the most attractive material in electronic device applications?</li></ul>	10
	c) What are applications of Oxidation process?	
	d) How are Resistors fabricated in monolithic IC?	
	e) Briefly discuss the basic structure of a MOS transistor?	
	f) Define noise margin?	
	g) What are lambda based designed rules?	
	h) What are various short channel effects in MOSFET?	
	<ul><li>i) What is a symmetrical CMOS inverter?</li><li>j) Why Domino logic is called high performance logic?</li></ul>	
	j) why bommo logic is called high performance logic?	
	Part A	
Q2)	a) Discuss crystal refining process in detail. What are various crystal defects?	5
	b) Discuss the Ion implantation process. Compare it with diffusion process.	5
Q3)	a) An enhancement type NMOS has the following parameters: $V_{To} = 0.8V$ , $\lambda = 0.05V^{-1}$ , $k' = 20\mu A/V^2$ . The current $I_D = 0.24mA$ when transistor is biased with $V_G = 2.8V$ , $V_D = 5V$ , $V_S = 1V$ and $V_B = 0V$ . Determine its W/L.	5
	b) Derive expression of maximum depletion depth in nMOS. What are various parameters on which the threshold voltage depends?	5
Q4)	a) Discuss the CMOS fabrication process steps. What is LOCOS?	5
<b>*</b> '/	b) Discuss the fabrication steps and diffusion profile of buried collector type BJT. What are its advantages over diffused BJT?	5
	Part B	
Q5)	a) Compare the nMOS and CMOS PTL in detail?	5
	b) Derive and analyze the expression for propagation delay (high to low) in CMOS inverter.	
		5
Q6)	a) Derive expression for dynamic power dissipation in CMOS. How can the power dissipation be reduced?	5
	-b) Derive the expression of logical threshold and V <sub>IH</sub> in CMOS inverter. Compare various inverter configurations.	5
Q7)	a) Discuss the implementation of XOR using PTL. Compare it in terms of	5
	number of transistors in the conventional CMOS implementation. b) Compare the Clocked CMOS and Conventional CMOS logic families.	5